

# Improving OLED performance via semiconductor dilution

**Chris Giebink**

Electrical Engineering Department  
Penn State University



**PennState**

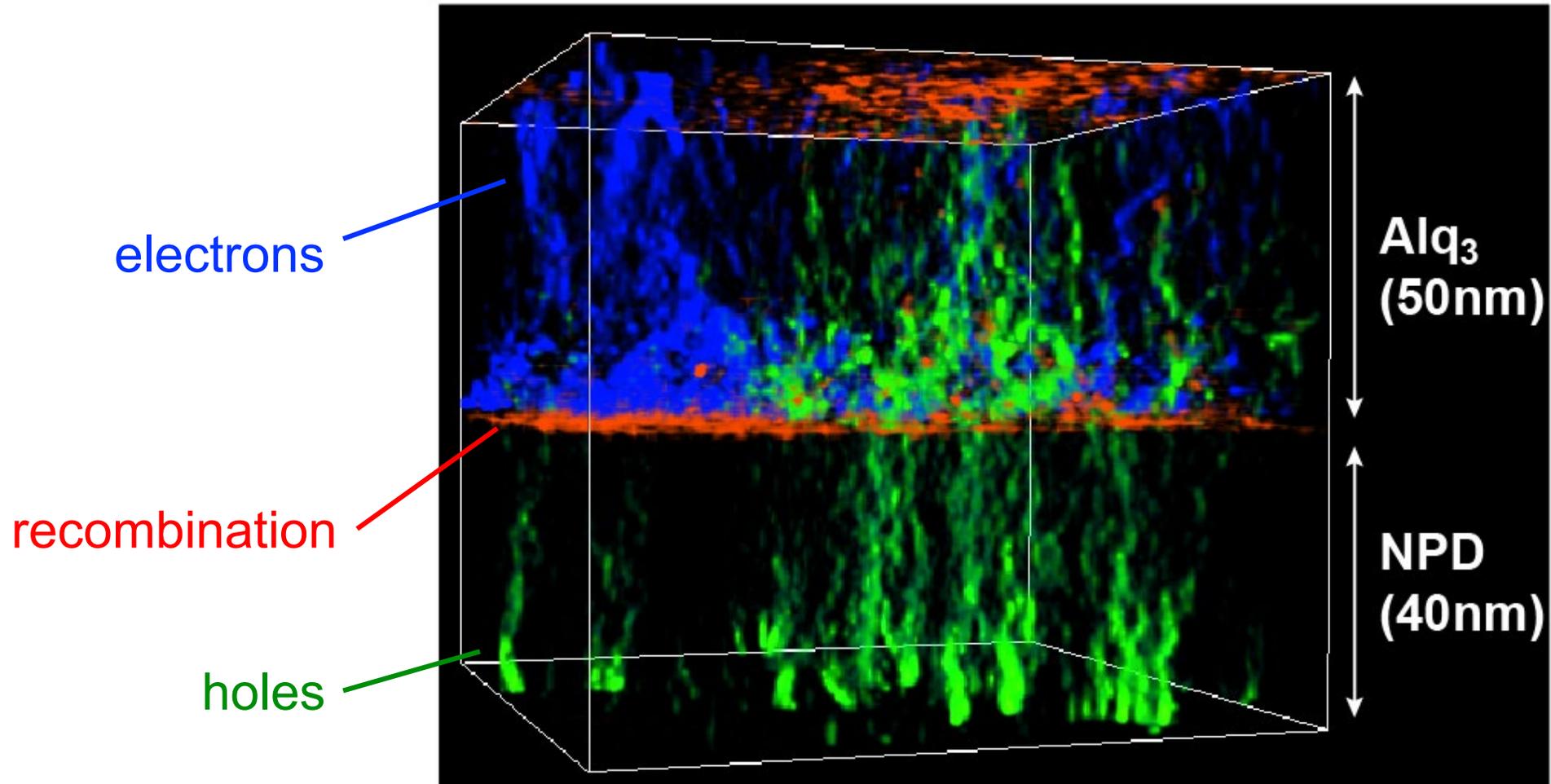
# 'Intrinsic' properties of OLED materials

- Refractive index  $n \sim 1.7$ 
  - Limits optical outcoupling efficiency
- Glass transition temperature  $T_g \sim 100-120^\circ\text{C}$ 
  - OLED panels operate at elevated temperature
  - Thermal stability closely connected to catastrophic failure
  - Intrinsic OLED lifetime  $\sim \exp(-E_A/kT)$



What if we could change properties like these without re-engineering OLED molecules?

# Most of the molecules aren't necessary



Transport is percolative, involves <5% of all molecules

# Semiconductor dilution

- Blending with insulating molecules can **improve** transport
- ...and change optical & morphological properties of the blend

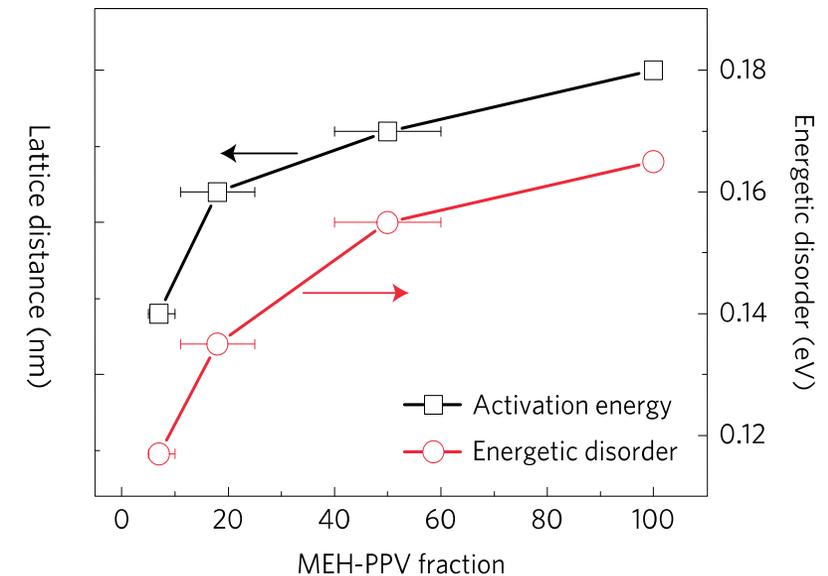
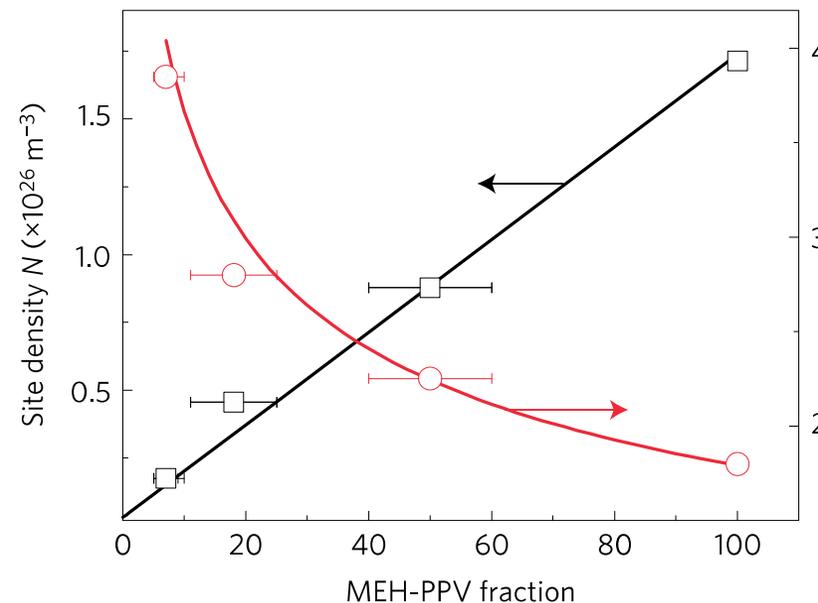
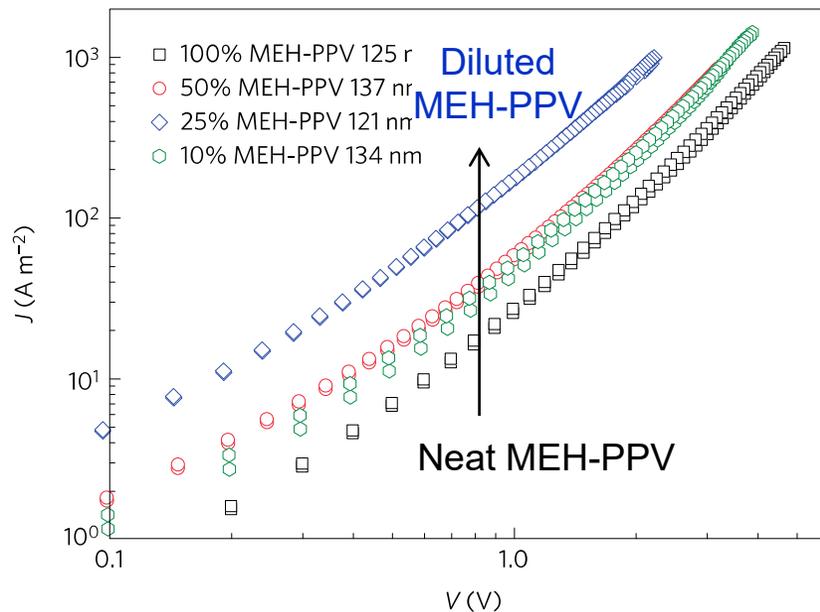
ARTICLES

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nature  
materials

## Elimination of charge carrier trapping in diluted semiconductors

D. Abbaszadeh<sup>1,2</sup>, A. Kunz<sup>3</sup>, G. A. H. Wetzelaer<sup>3</sup>, J. J. Michels<sup>3</sup>, N. I. Crăciun<sup>3</sup>, K. Koynov<sup>3</sup>, I. Lieberwirth<sup>3</sup> and P. W. M. Blom<sup>3\*</sup>



Replace ~half your organic semiconductor w/o sacrificing electrical transport

# Semiconductor dilution

- Blending with insulating molecules can **improve** transport
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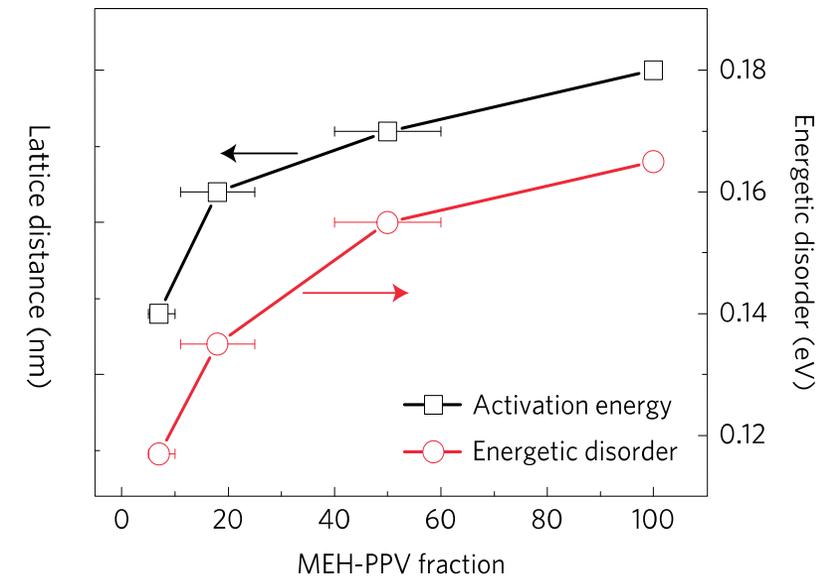
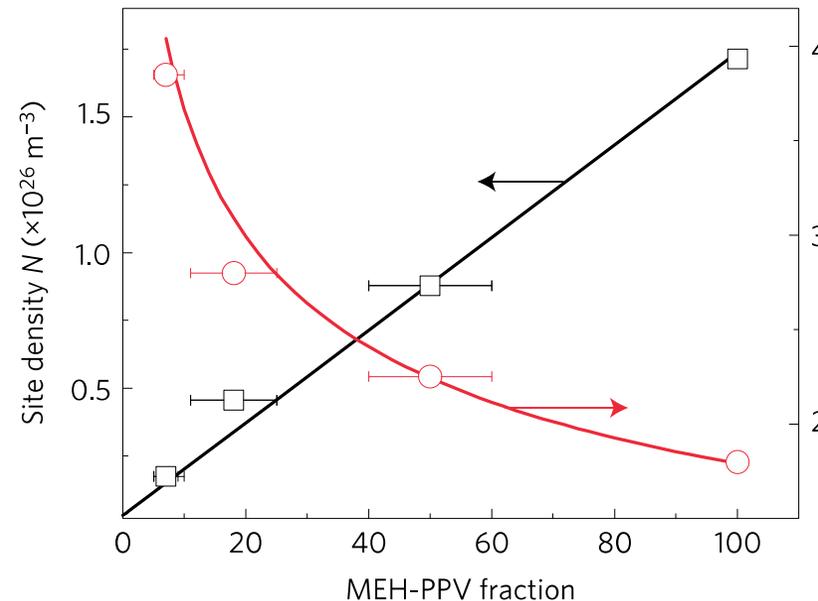
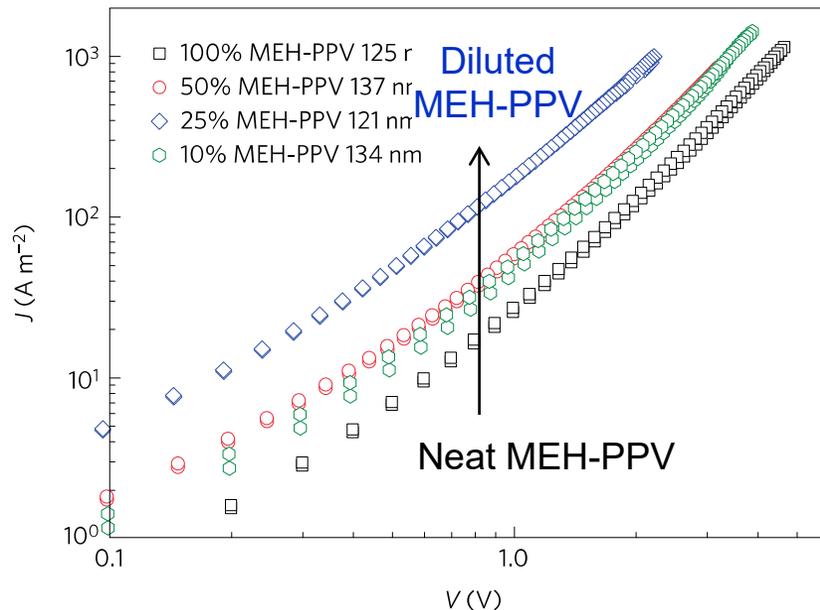
## GENERAL FEATURES

The temporal features of the current transients  
 The nondispersive to dispersive (ND → D) transition  
 Summary

(Older dilution)

## EXPERIMENTAL

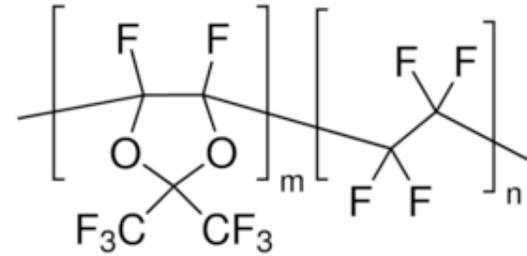
The field dependencies of the mobility  
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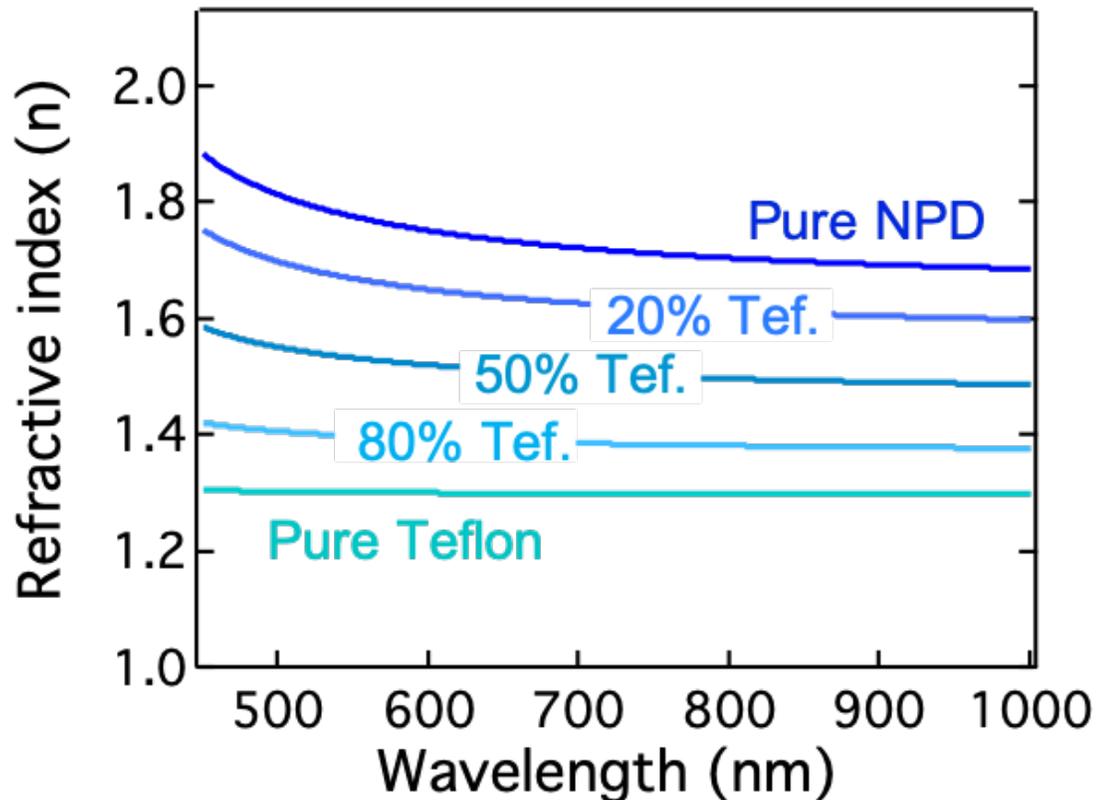
Replace ~half your organic semiconductor w/o sacrificing electrical transport

# Changing blend properties with Teflon AF

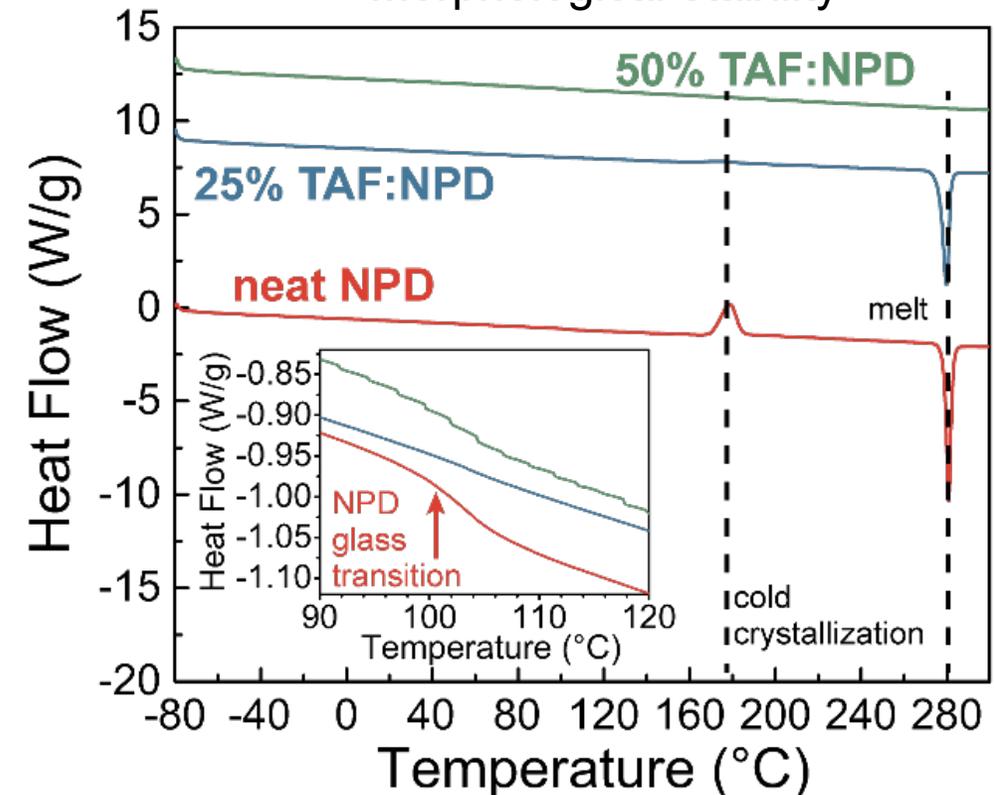
- Co-evaporate Teflon AF w/ small molecules



Refractive Index

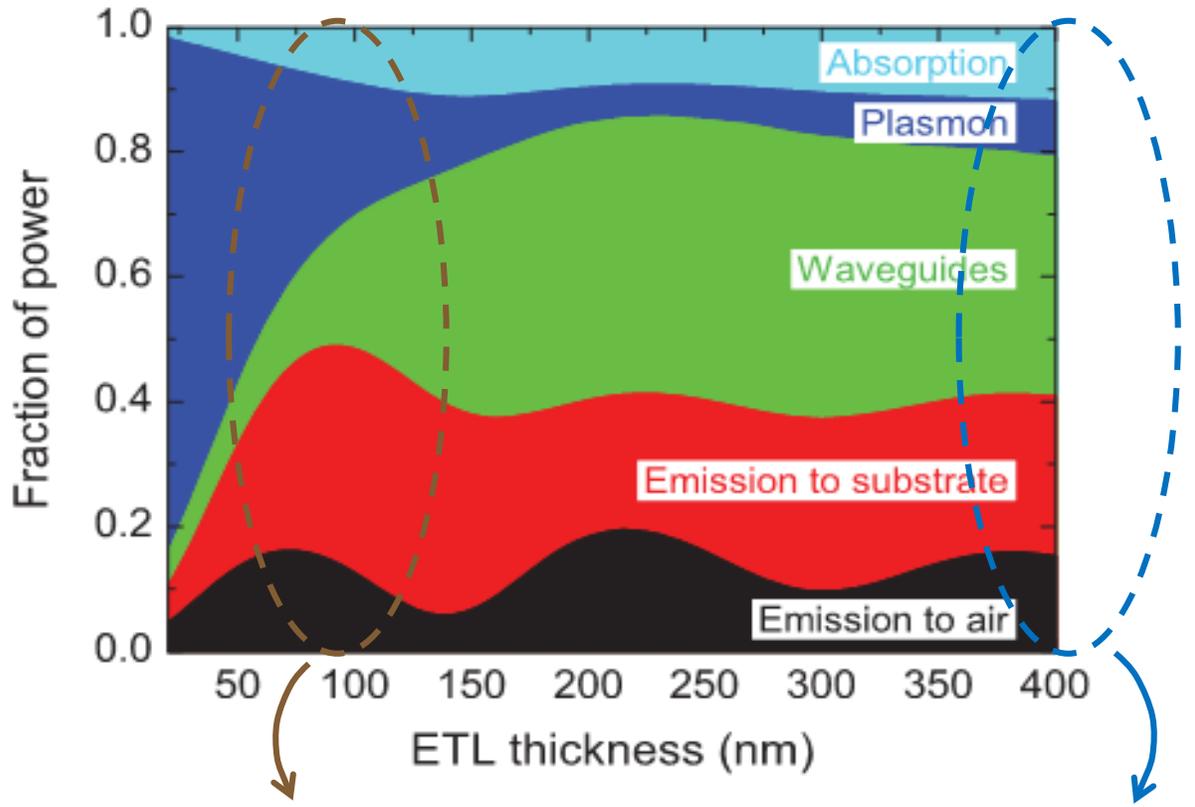


Morphological stability



# Opportunity for outcoupling

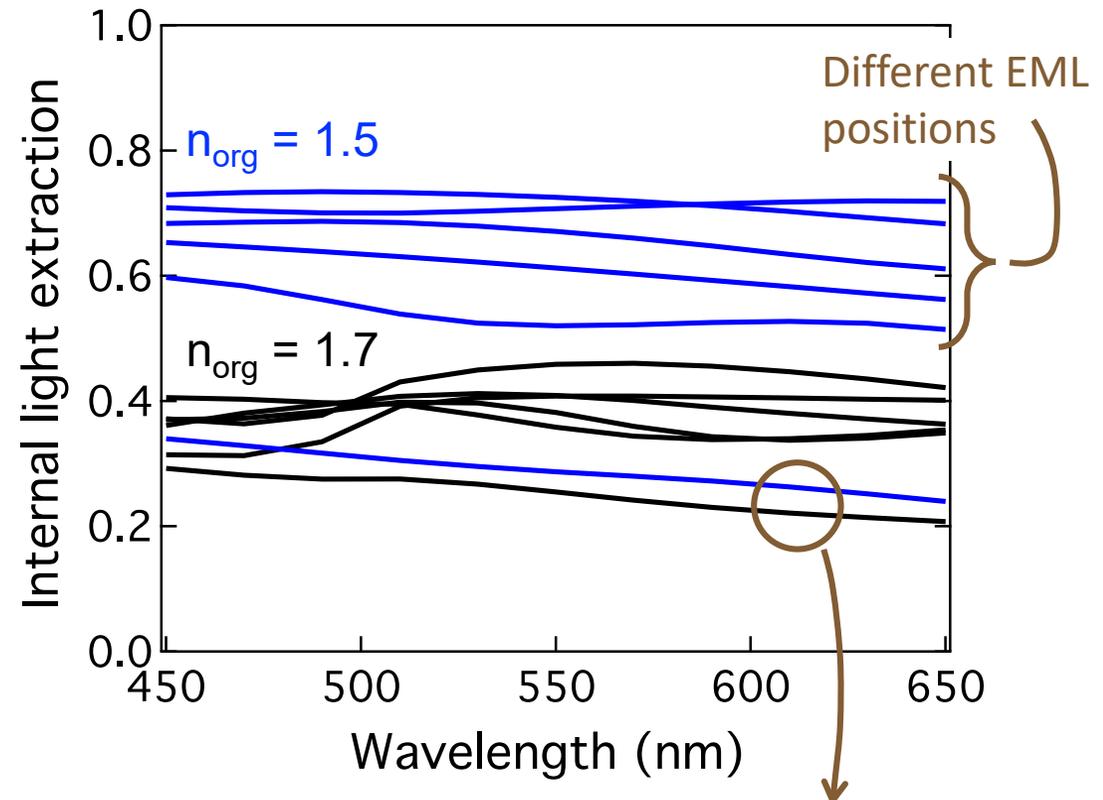
- Guided mode loss dominates in multi-stack WOLEDs



Focus of most outcoupling work

Regime that matters for commercial WOLEDs

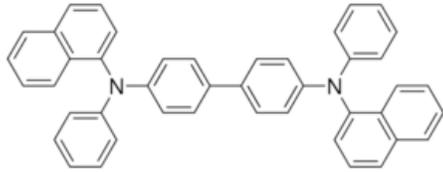
- 6-stack WOLED: Dropping index significantly increases ILE



EML closest to cathode

# What happens to electrical transport?

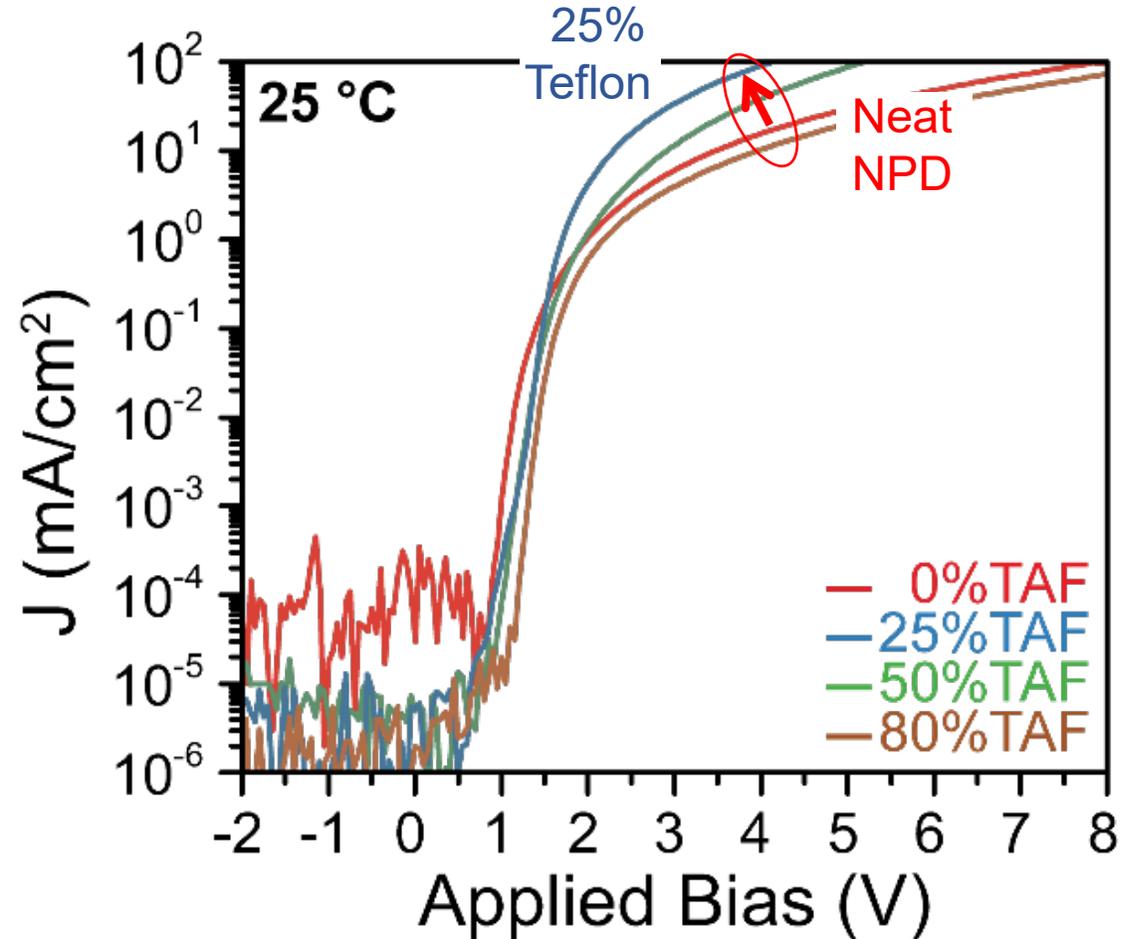
- Hole-only devices:



$T_g \sim 95^\circ\text{C}$

ITO	TAF:NPD (60 nm)	Al (100 nm)
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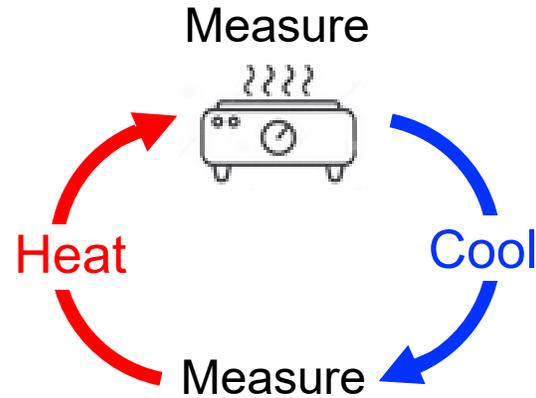
	Drive voltage @ 10 $\text{mA}/\text{cm}^2$
Neat NPD	$3.5 \pm 0.1$
25% TAF:NPD	$2.3 \pm 0.1$
50% TAF:NPD	$2.9 \pm 0.1$
80% TAF:NPD	$4.0 \pm 0.1$



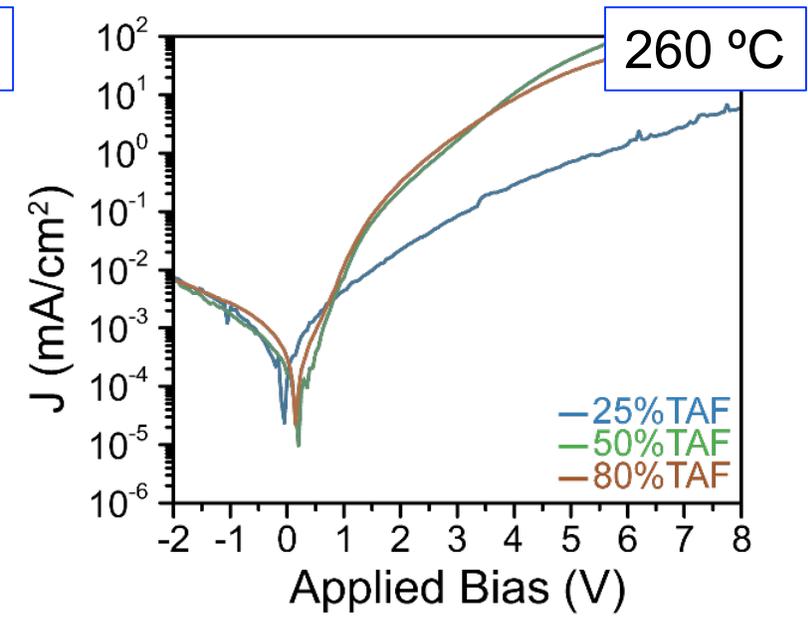
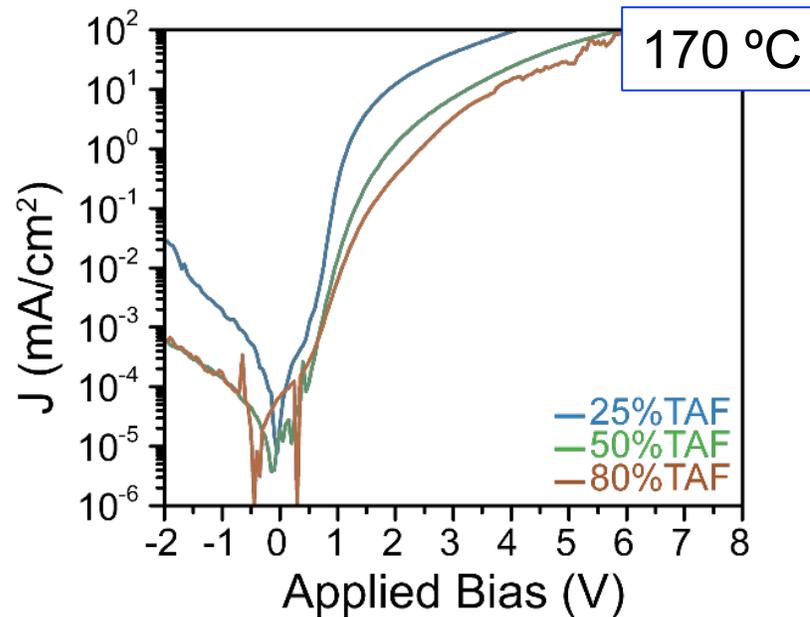
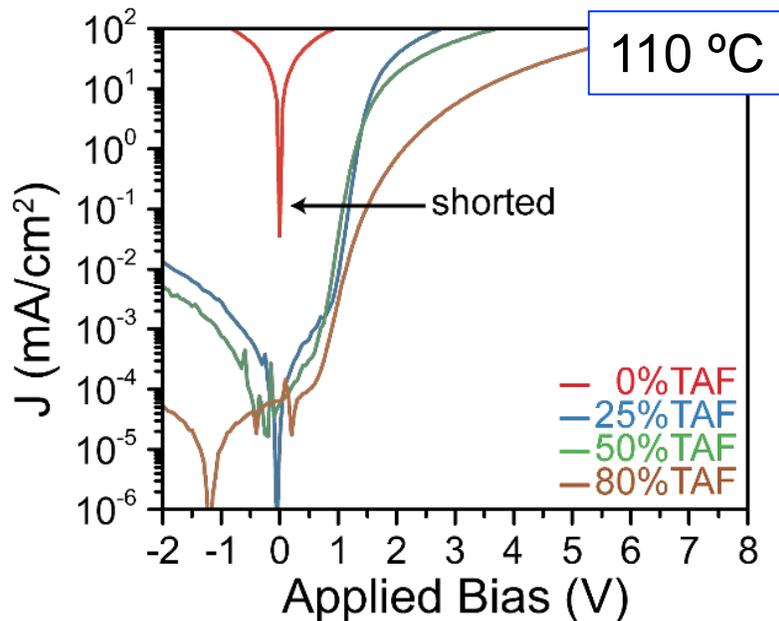
Decreases drive voltage for up to 50% Teflon:NPD

# High temperature performance

- Teflon-blended devices don't short
- Maintain rectification above 250°C



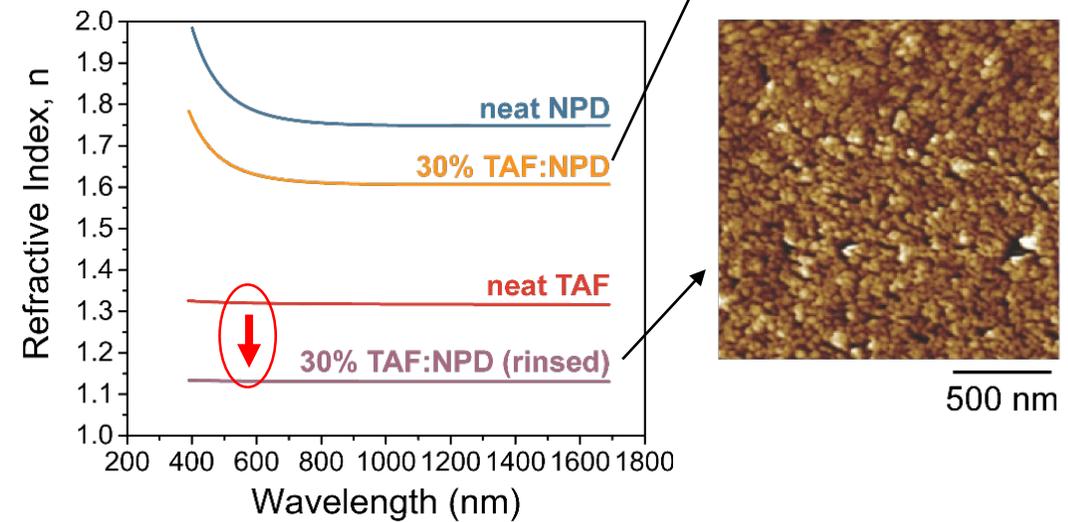
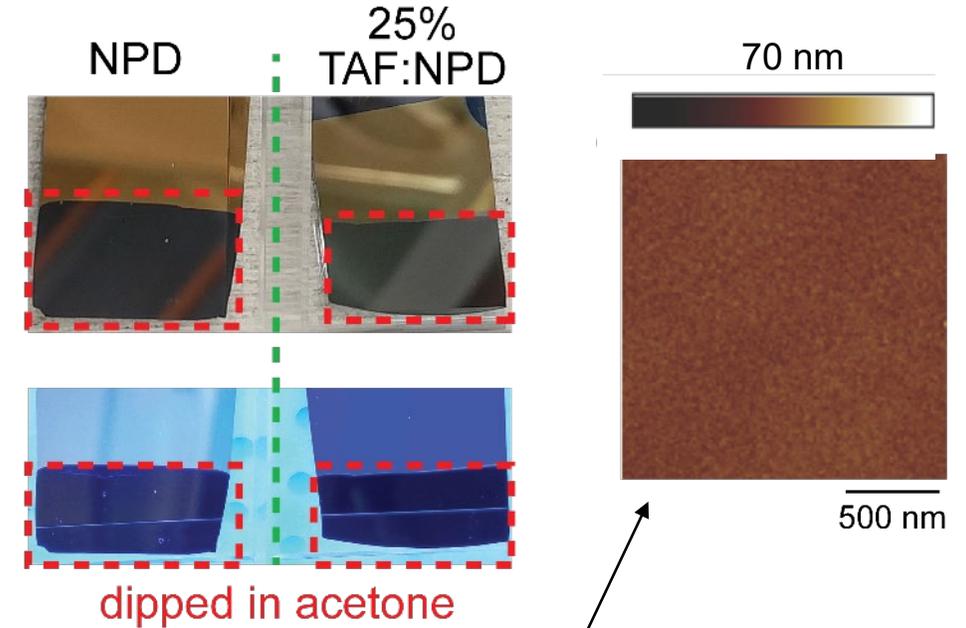
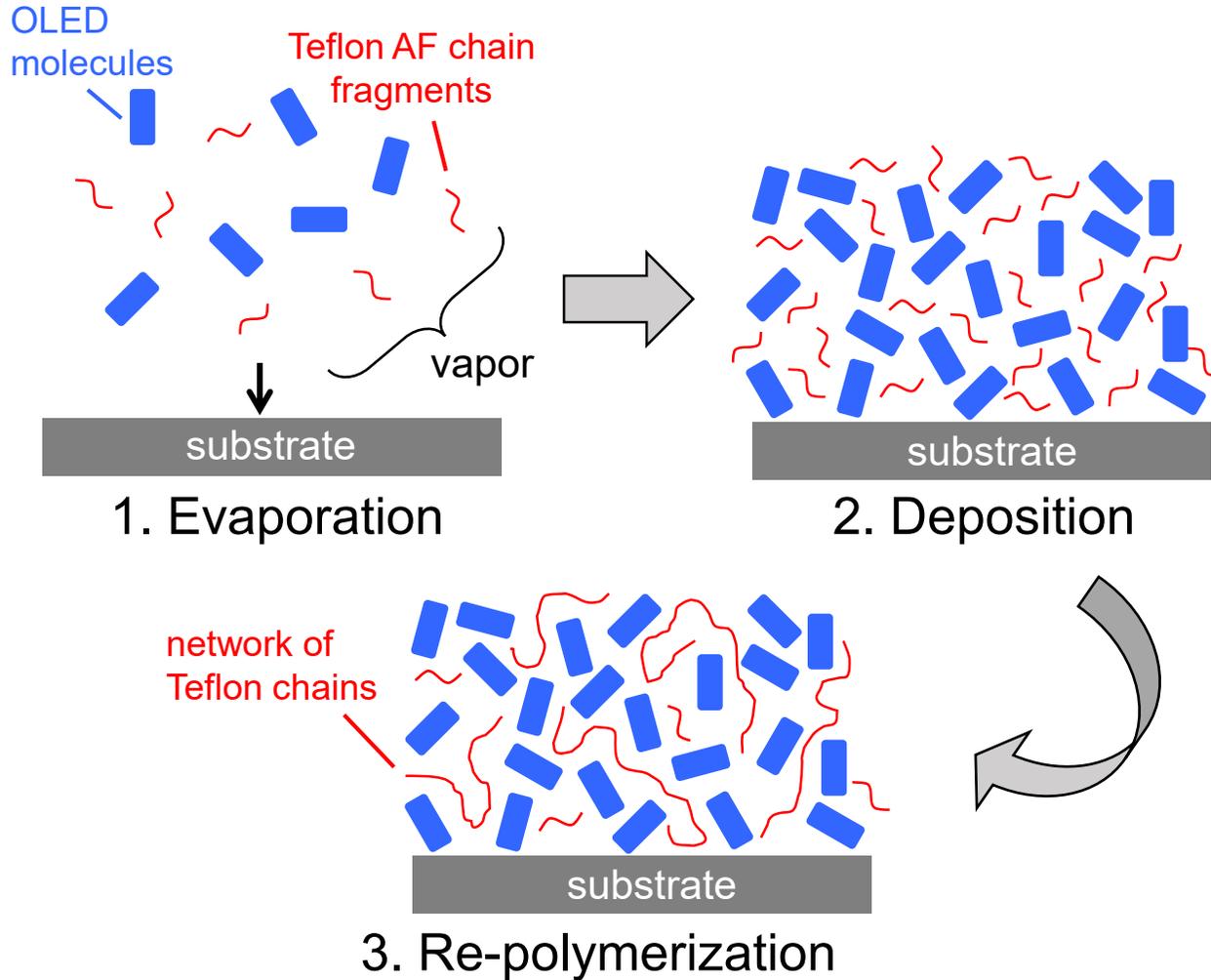
	Catastrophic failure temp.
Neat NPD	110 °C
25% TAF:NPD	260 °C
50% TAF:NPD	>260 °C
80% TAF:NPD	>260 °C



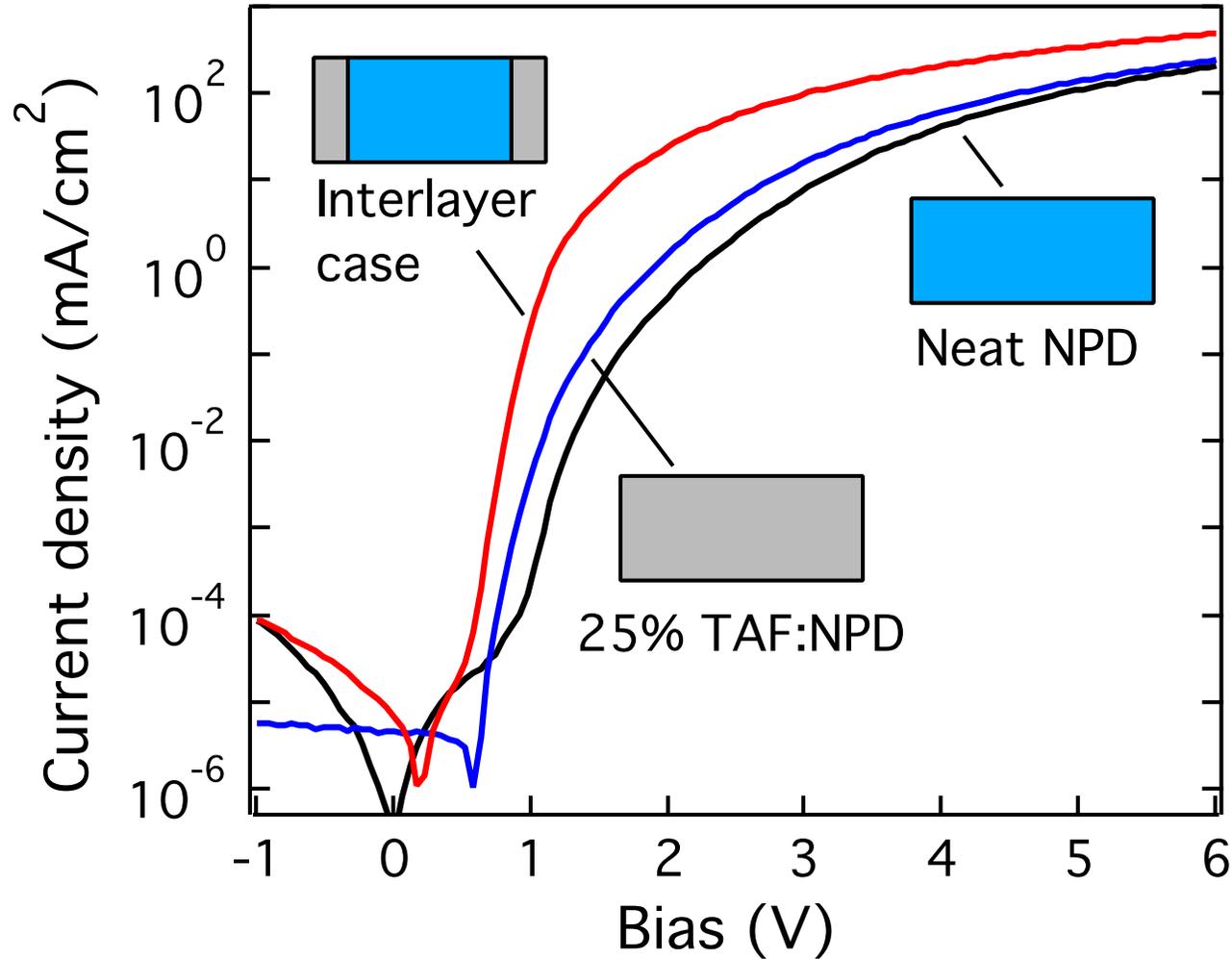
Increases thermal stability of diodes to >250°C

# How we think it works

- Analogy to fiberglass:



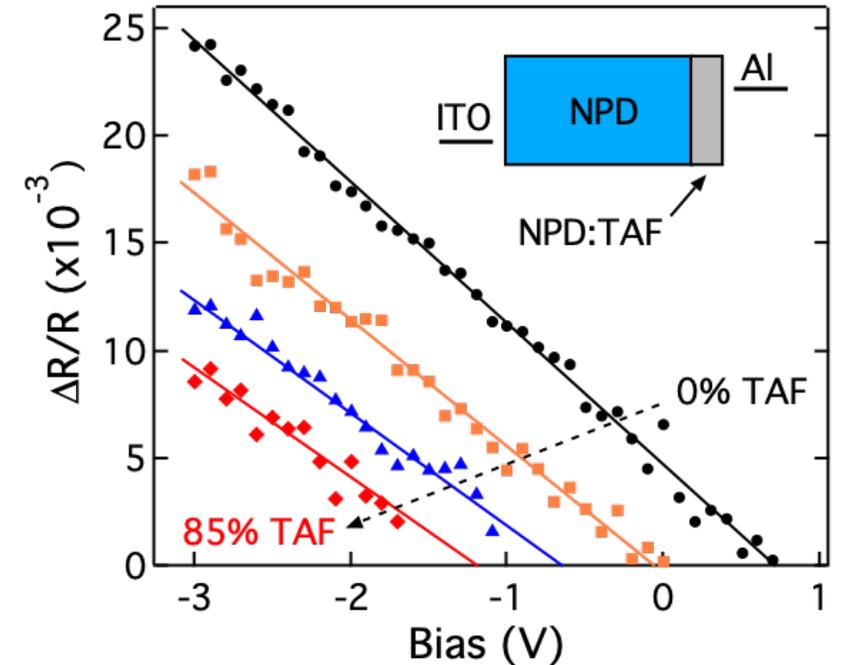
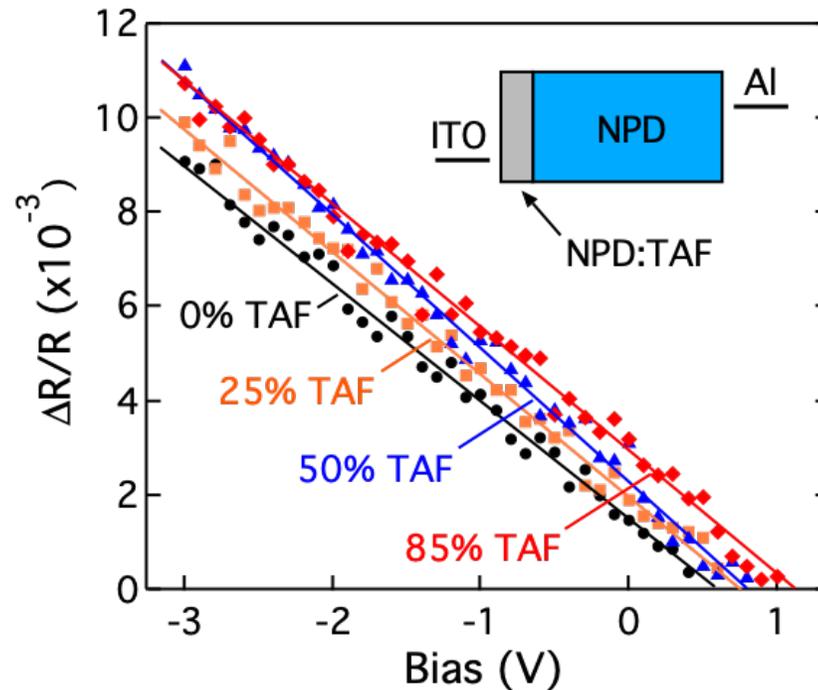
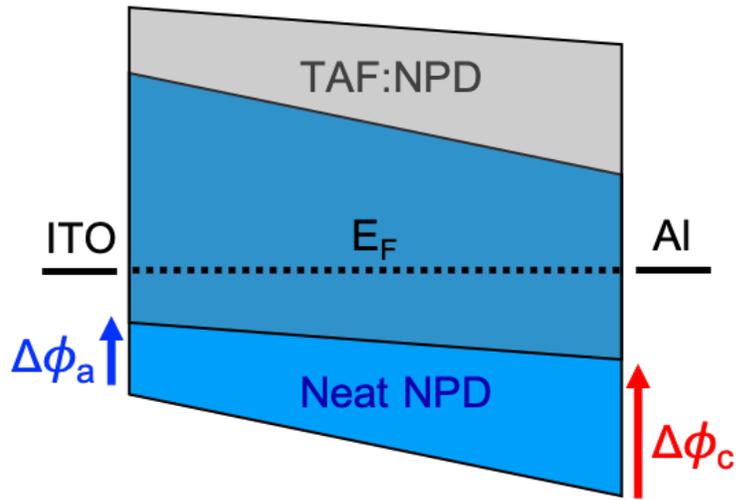
# Injection or bulk transport effect?



Injection improves, bulk transport degrades

# Interface energetics

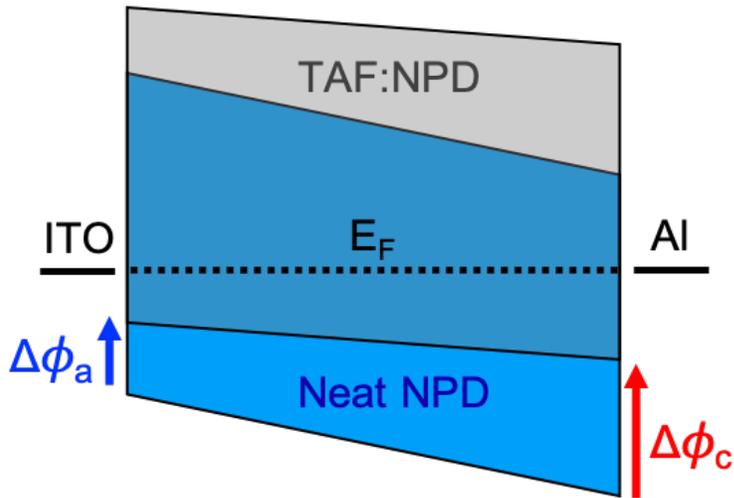
- Electroabsorption to measure changes in  $V_{bi}$ :



Interface dipoles shift HOMO up at both anode & cathode

# Interface energetics

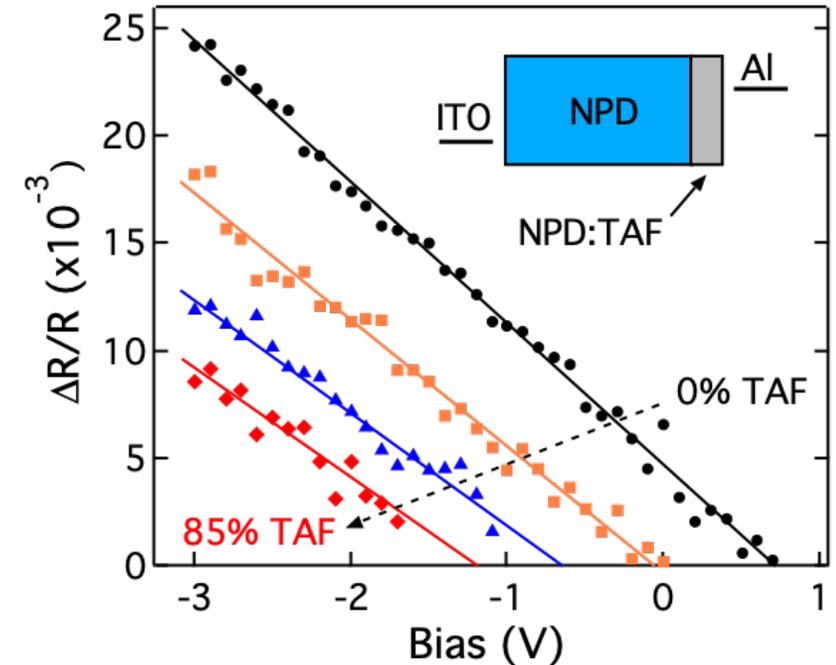
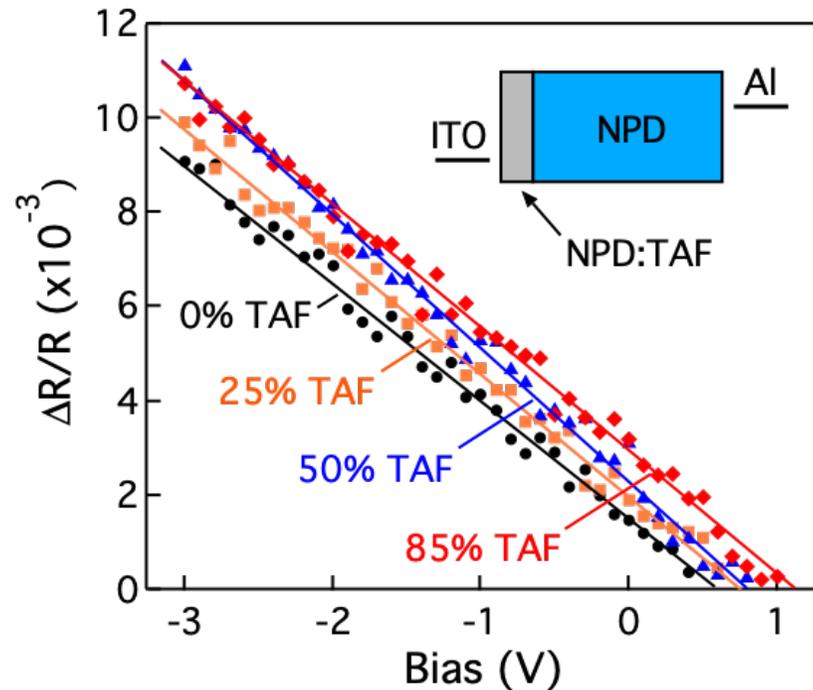
- Electroabsorption to measure changes in  $V_{bi}$ :



## Anode/organic interface modification by plasma polymerized fluorocarbon films

J. X. Tang, Y. Q. Li, L. R. Zheng, and L. S. Hung<sup>a)</sup>

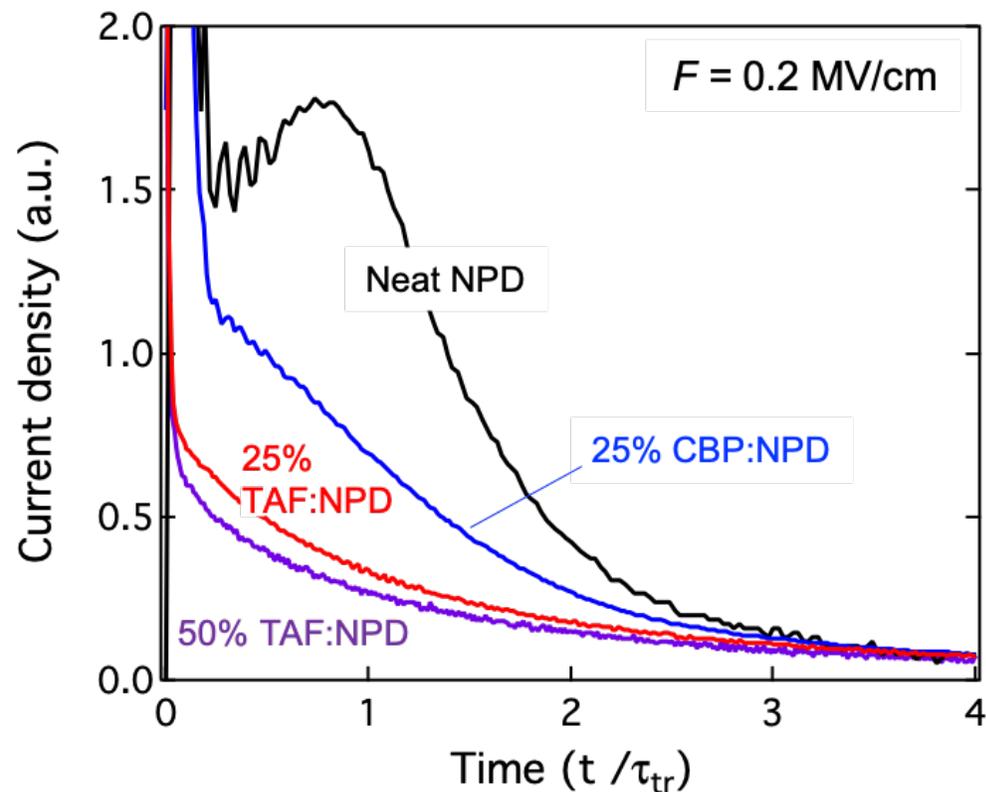
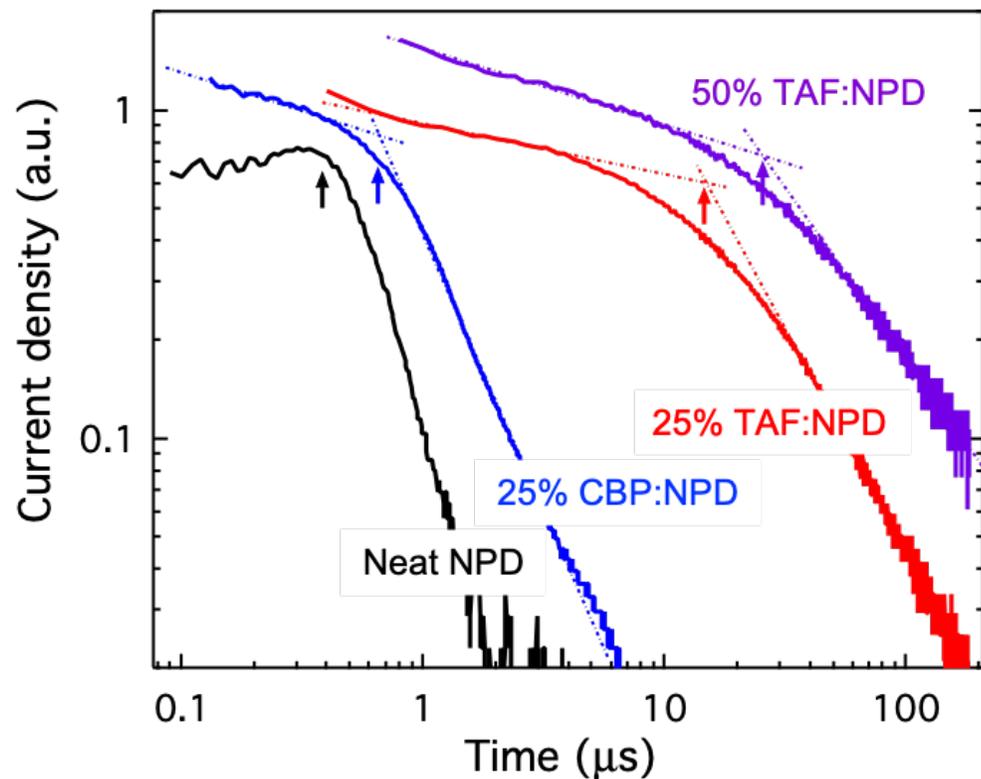
*Department of Physics & Materials Science, City University of Hong Kong, Hong Kong, China*



Interface dipoles shift HOMO up at both anode & cathode

# Bulk transport?

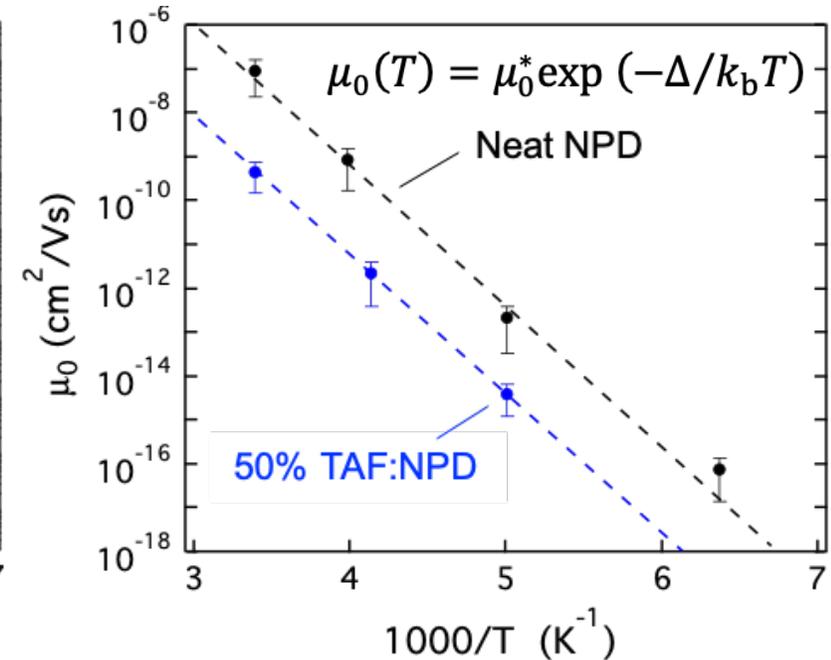
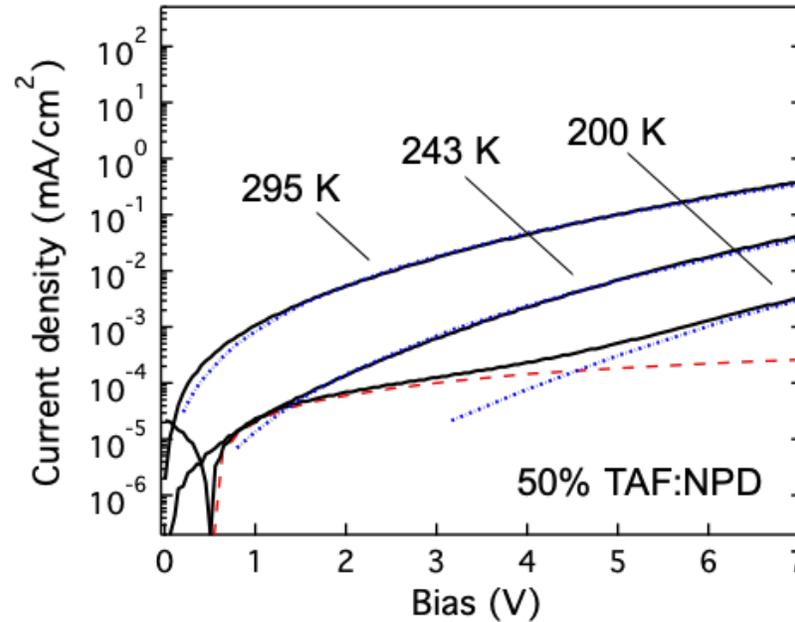
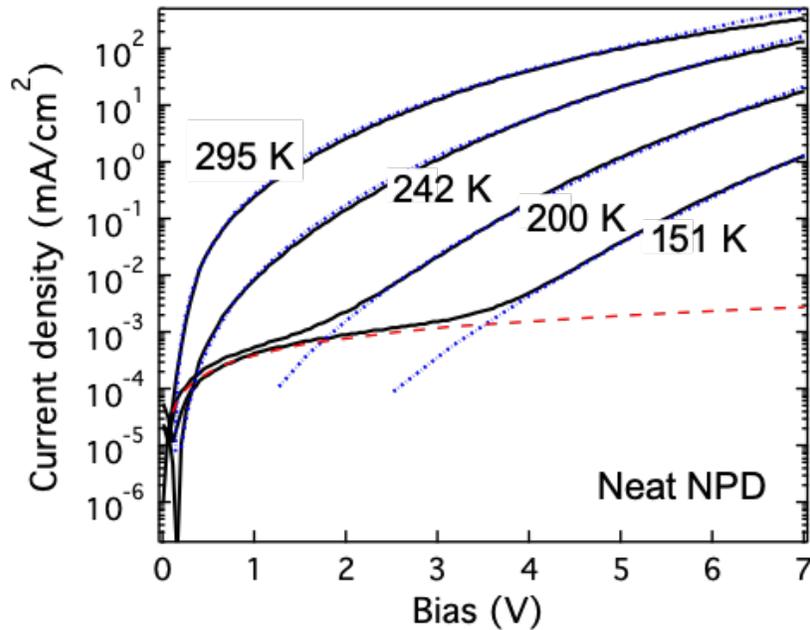
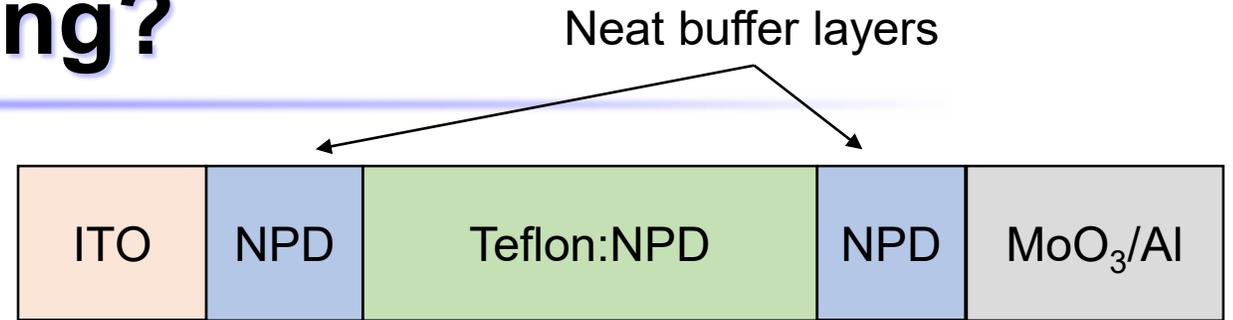
- Time-of-flight mobility:



Hole mobility becomes dispersive, decreases  $\sim 50$ -fold

# Energetic disorder/trapping?

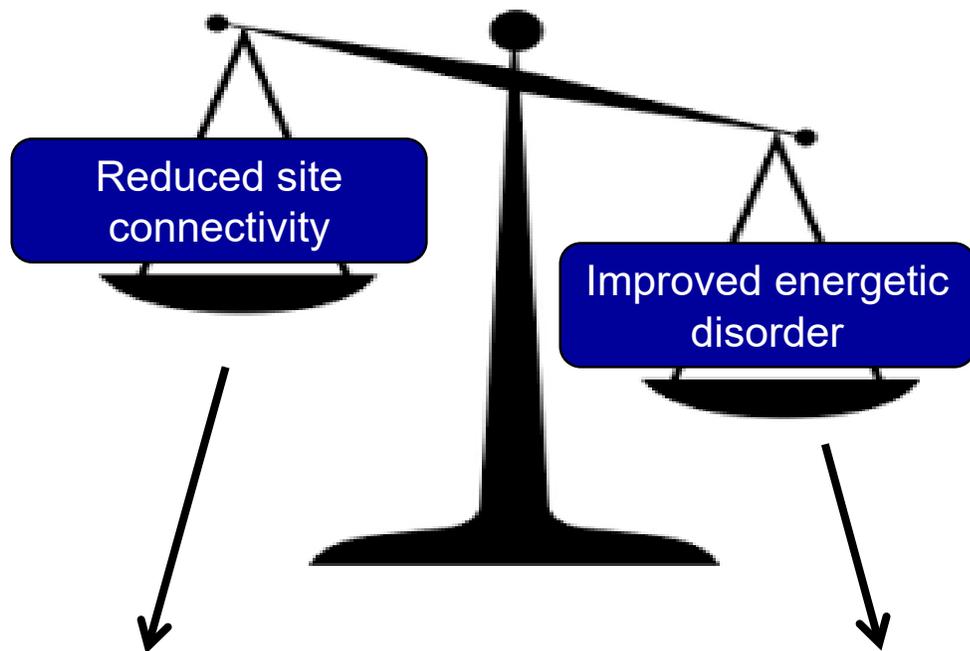
- Temperature-dependent IVs:



Mobility activation energy is the same → reduced site density/percolation

# Prospects for improvement?

- Genuine dilution is non-trivial

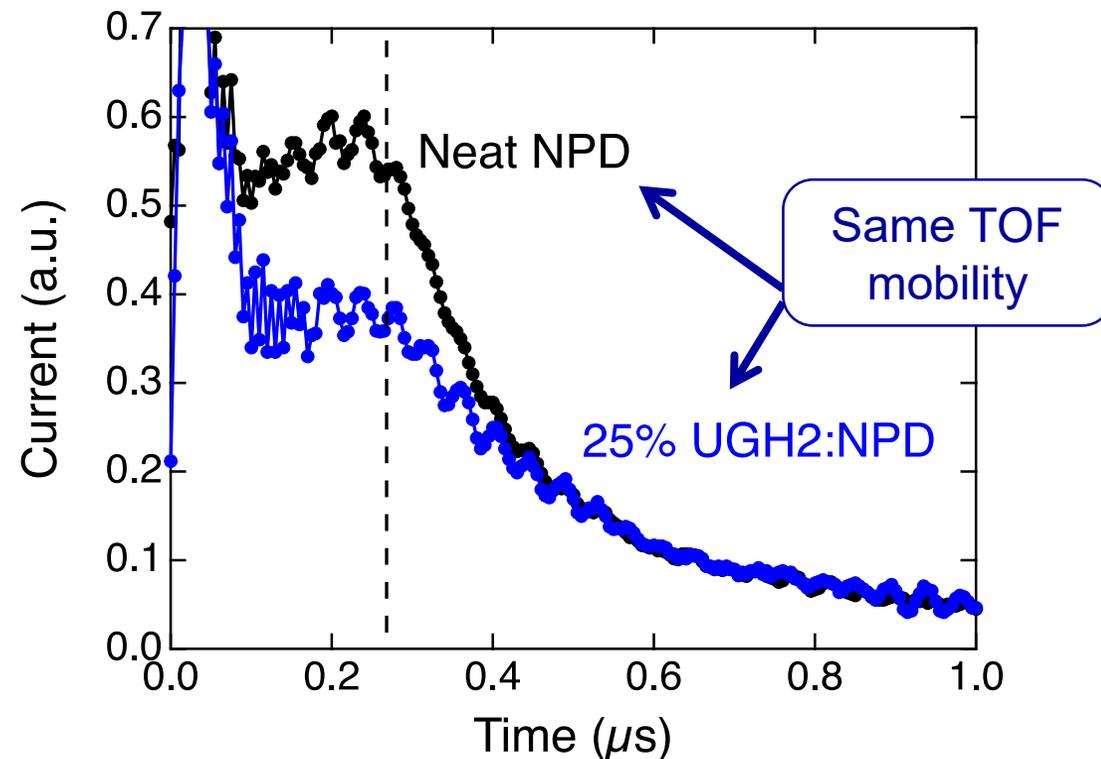


- Percolation
- Blend morphology

- Relative dipole moments
- Relative polarizabilities

Other considerations

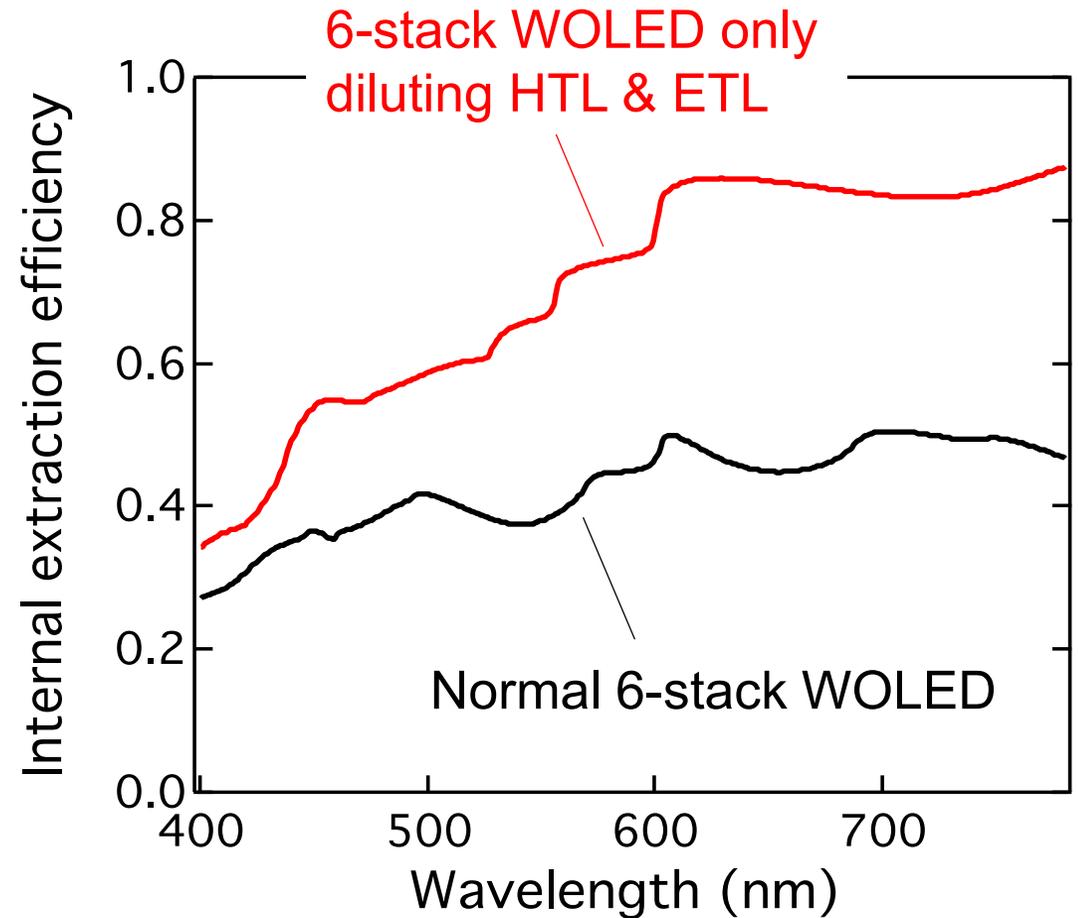
- Optical properties (lower  $n$ )
- Thermal properties (higher  $T_g$  blends) ...



# Questions for the community

- What if we could tailor  $\mu$  and  $n$  in every transport layer of a WOLED stack?
  - What does the grand electrical & optical optimization look like?
  - What does the magic dilution molecule look like? (We don't want Teflon AF)
  - Is there economic value in displacing the cost of 'expensive' organic semiconductors?

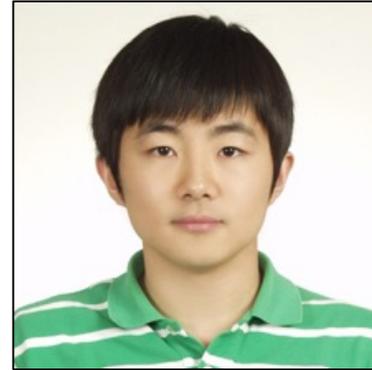
Should dilution molecules become another standard ingredient for OLEDs?  
(like emitters, HTMs, ETMs, HBLs, EBLs, etc)



# Acknowledgements

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- Christian Ruud
- Emmanuel Afolayan



- **Collaborators**

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